风光欣技术资料

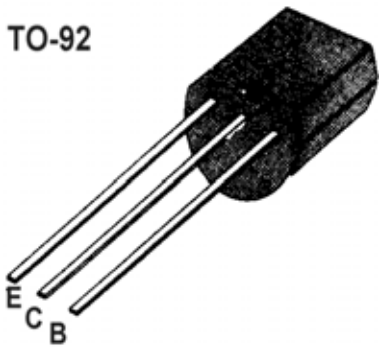
B1277

—PNP silicon —

■■**APPLICATION**：Audio power amplifier, High current application.

■■**MAXIMUM RATINGS（Ta＝25℃）**

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-2	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃



■■**ELECTRICAL CHARACTERISTICS（Ta=25℃）**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	100		320		V_{CE}= -2V，I_C= -500mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -30V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -5V，I_C=0
Collector-Base Breakdown Voltage	BV_{CBO}	-30			V	I_C= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-30			V	I_C= -10mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -1mA，I_C=0
Base-Emitter on Voltage	$V_{BE(ON)}$			-1	V	V_{CE}= -2V，I_C= -500mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.8	V	I_C= -2A，I_B= -200mA
Gain bandwidth product	f_T	100	170		MHz	I_C= -50mA，V_{CE}=-5 V
Common Base Output Capacitance	C_{ob}		48		pF	V_{CB}= -10V, I_E=0, f = 1MHz

■■h_{FE} **Classification**

Classification	O	Y
h_{FE}	100~200	160~320